

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **D1-28Z** is Designed for General Purpose Class C Amplifier Applications up to 1.0 GHz.

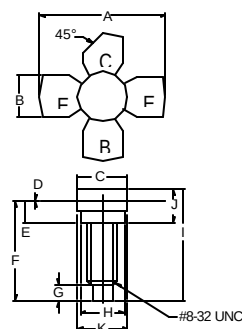
FEATURES:

- $P_G = 8.0$ dB Typ. at 1 W/1,000 MHz
- Emitter Ballasting for Ruggedness
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	1.0 A
V_{CB}	45 V
P_{DISS}	7 W @ $T_C = 25^\circ\text{C}$
T_J	-65 to +200 $^\circ\text{C}$
T_{STG}	-65 to +150 $^\circ\text{C}$
θ_{JC}	25 $^\circ\text{C/W}$

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

ORDER CODE: ASI10807

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1$ mA	45			V
BV_{CER}	$I_C = 20$ mA $R_{BE} = 10 \Omega$	45			V
BV_{EBO}	$I_E = 1$ mA	3.5			V
I_{CBO}	$V_{CE} = 28$ V			250	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	15		150	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz			5.0	pF
P_G	$V_{CE} = 28$ V $P_{OUT} = 1.0$ W $f = 1,000$ MHz	7.0	8.0		dB
h_c		65			%